



# COUPON AND CAVITY STUDIES OF SRF THIN FILMS

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## PRODUCED BY ENERGETIC CONDENSATION\*

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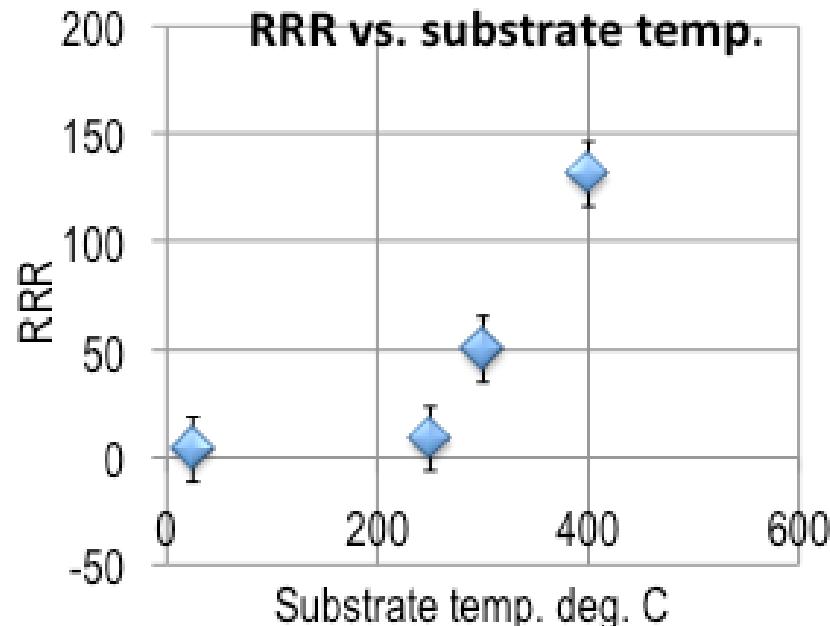
# *Approach of the AASC-JLab/NSU collaboration*

- ◆ Use CED™ and FCAD techniques to coat sapphire and Cu coupons
- ◆ Use surface analysis techniques at JLab/NSU to characterize morphology
- ◆ Measure RRR and  $T_c$  from sapphire coated coupons
- ◆ Use SIC facility at JLab to measure impedance of films in cavity
- ◆ Improve our understanding of the relationships between surface characteristics and superconducting properties

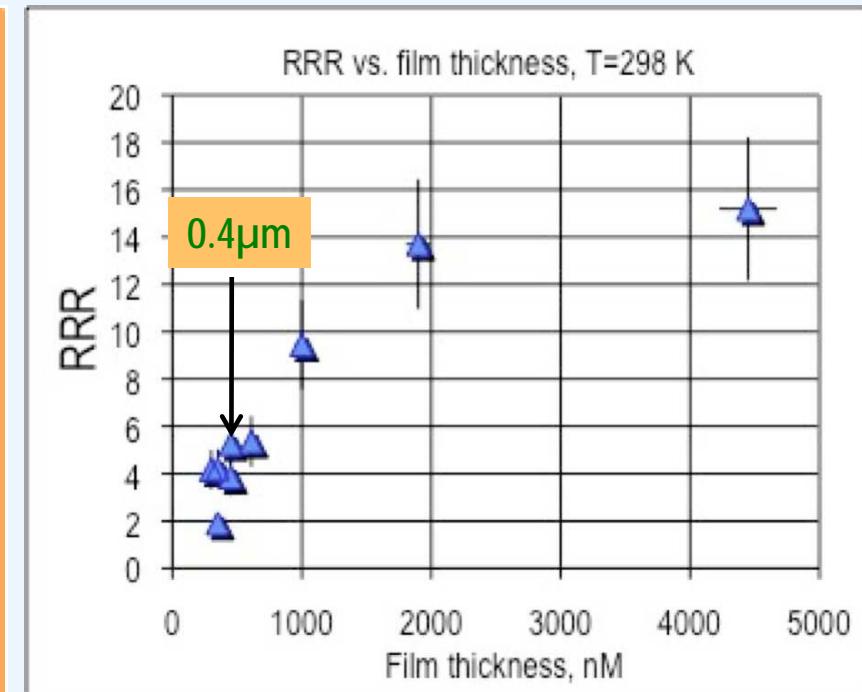


*RRR of 131 measured in thin film Nb  
deposited by CED<sup>TM</sup>*

*Is RRR~300 possible?*



Strong RRR variation for fixed thickness  
( $0.4\mu\text{m}$ ) and variable substrate  
temperature



Strong RRR variation with film thickness at  
fixed temperature (25 deg. C)

- ◆ We are growing thicker films at higher temperature to see if RRR increases

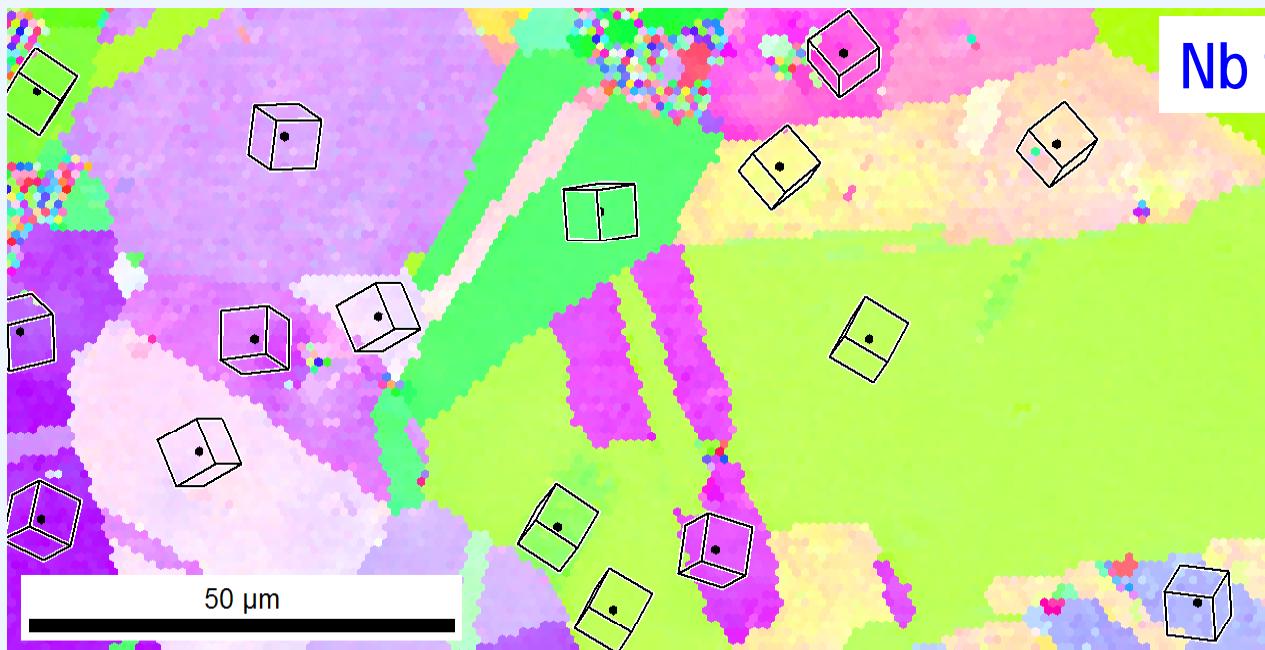


# A survey of RRR from various Nb thin films

RRR	Thickness	Method	Substrate . Temp.	Substrate	Reference
2		Magnetron Sputtering	R.T.	sap. quartz, Cu	Russo, SC. Sci. Technol. 18 (2005) L41-44, P43
40			200 °C		Russo, Meas. Sci. Tech [18. (2007) 2299-2313, p2302
50	0.8-1.1µm	Cathodic Arc	R.T. 150 °C	Sapphire, Bias - 80V	Russo, "2LX02", (2008)
50	235nm	ECR plasma (JLab)	R.T.	Sapphire, bias - 51V	Genfa Wu, Thin Solid Films, 489 (2005) 56 - 62, p 58
87	600nm	Evap. Epitaxy	850 °C	Sapphire Orient. [0,1,-1,0] Nb. Or. [211]	Wolf, J.Vac. Sci. Tech. A., Vol4, No.3., May/Jun (1986), p 526.
130	400 nm	CED™ (Cathodic Arc, AASC)	400 °C	Sap. A-plane, 400 C, no bias	AASC, JLab. (2009)

*~50 $\mu$ m grains of Nb measured in 0.4 $\mu$ m  
thick films on Cu*

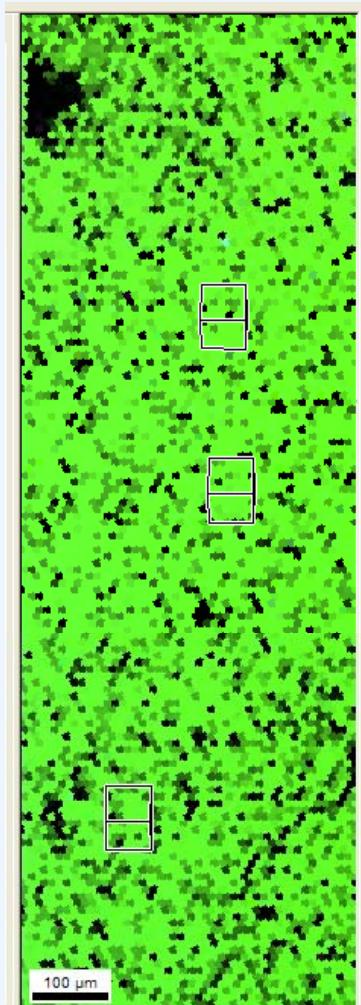
# CED™ Nb Film on polycrystalline Cu substrate: Hetero-epitaxy?



*Nb crystal structure also shows strong dependence on substrate temperature*

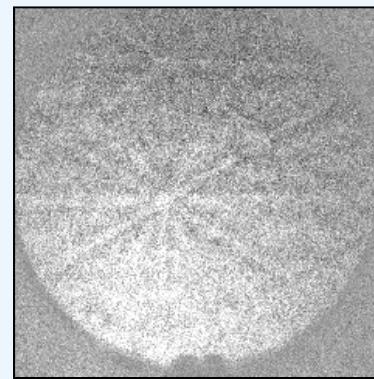
Substrate T = 300°

Sample: AASC-126-015



Avg. C.I. 0.44,  
Max CI 0.96

Both figures are in IPF+CI  
view (CI grayscale range 0-0.4)

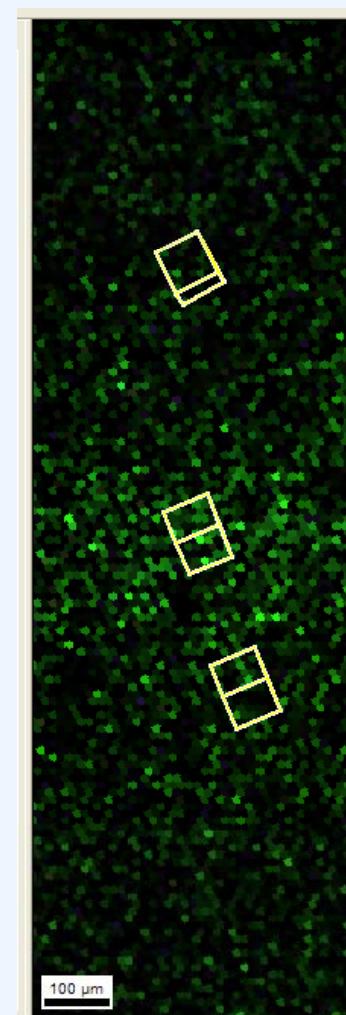


aasc-126-nb-015-1\_r0c32.jpg

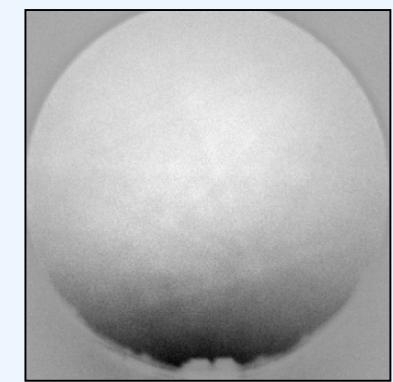
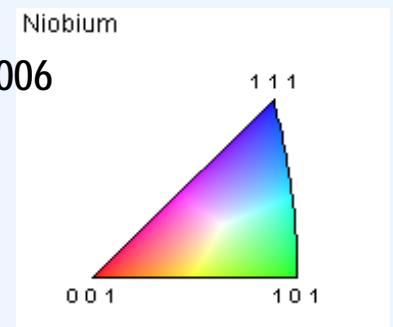
The sample had very sharp  
Kikuchi patterns. It has  
monolithic crystal structure  
Nb (110)

Substrate T = 25°

Sample: AASC-126-006



Avg. C.I. 0.04, Max CI 0.43



aasc-126-006 180x\_r126c33.jpg

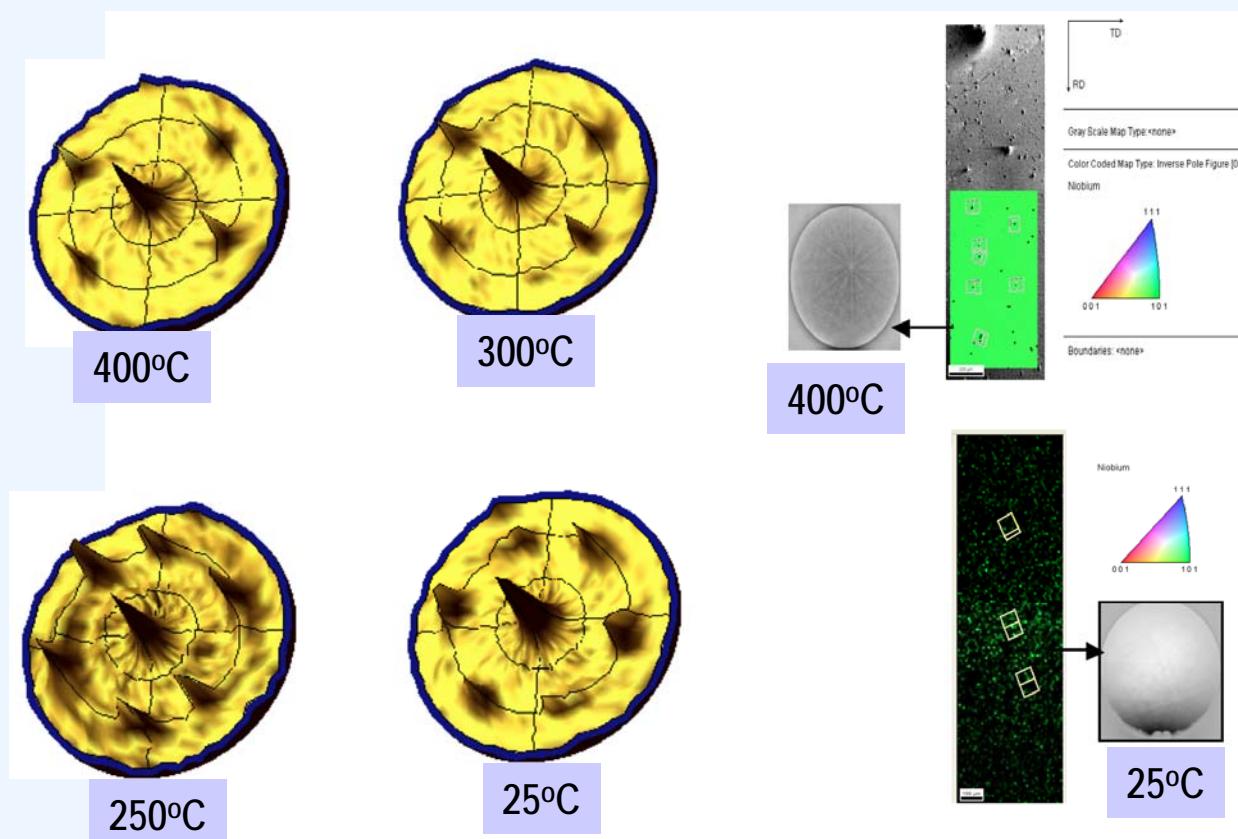
The sample had very  
faint Kikuchi patterns.  
It has uneven  
monolithic crystal  
structure Nb (110)

# XRD Pole figures: 25°C, 250°C, 300°C & 400°C

TABLE I. Summary of Nb films on a-plane Al<sub>2</sub>O<sub>3</sub> substrate for crystallographic and electrical properties

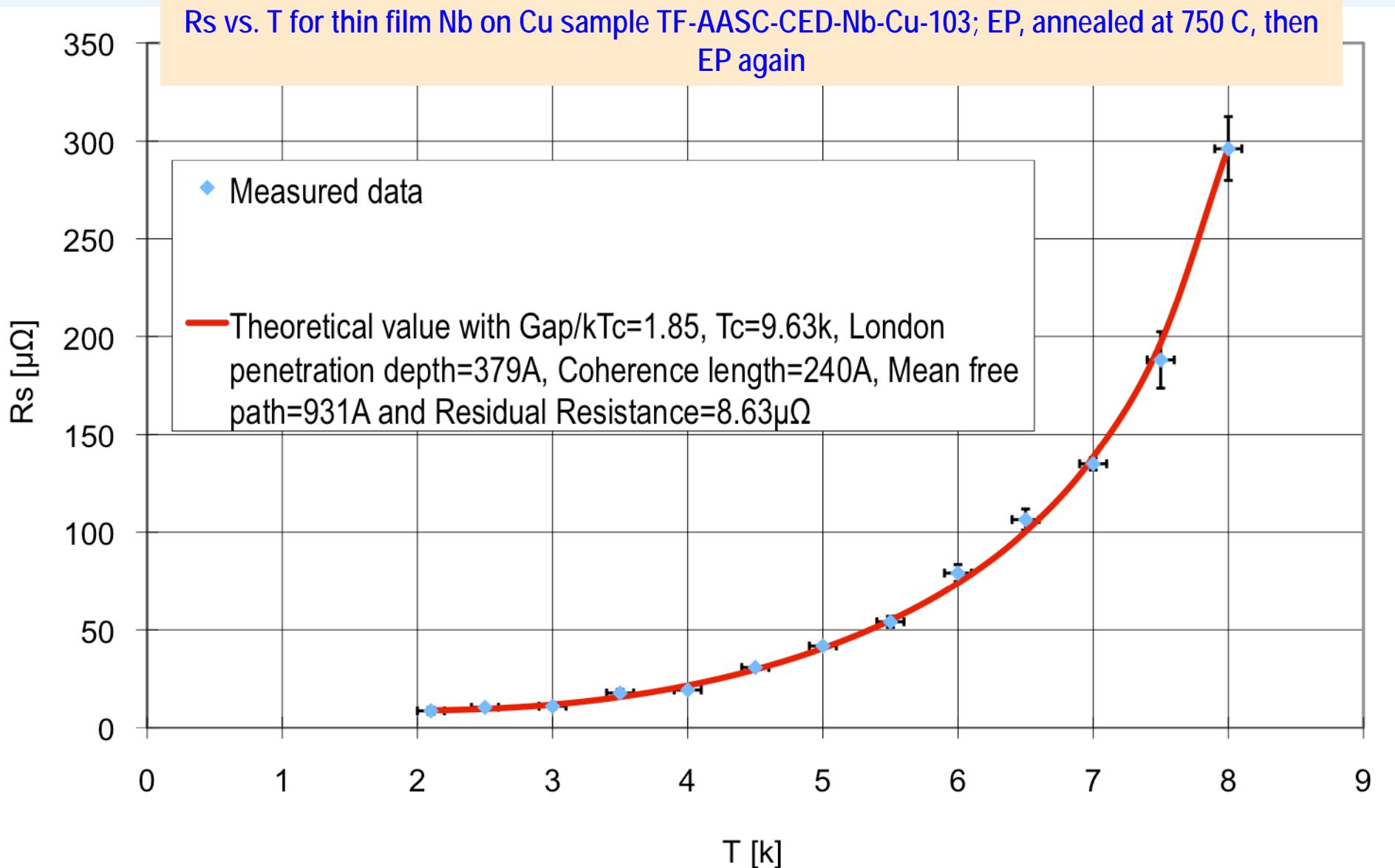
Ts	out-of-plane XRD	Pole figure	EBSD	RRR
400°C	(110)	single	Kikuchi pattern	129
300°C	(110)	single	Kikuchi pattern	50
250°C	(110)	twin	•	9
25°C	(110)	twin	no Kikuchi pattern	4

Ts; substrate temperature, RRR; the ratio of residual resistivity





# *JLab SIC cavity is a useful tool*

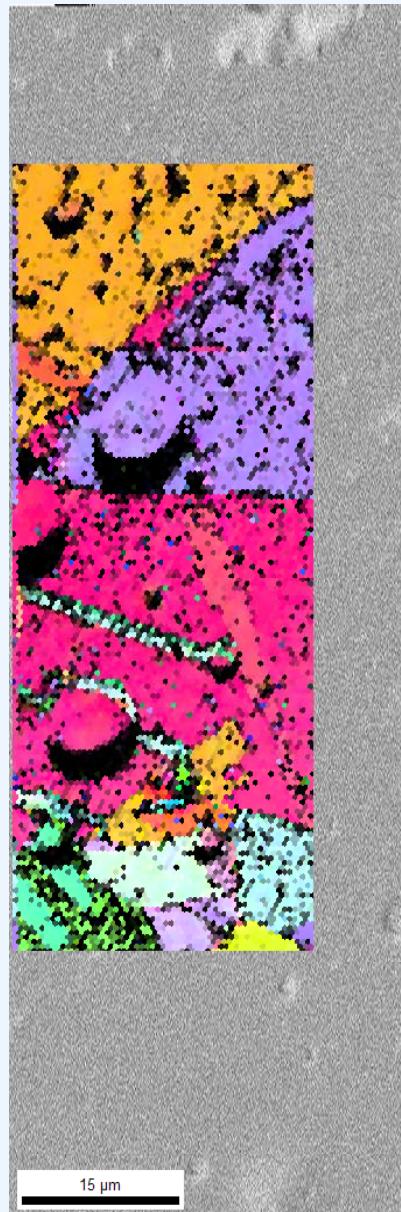
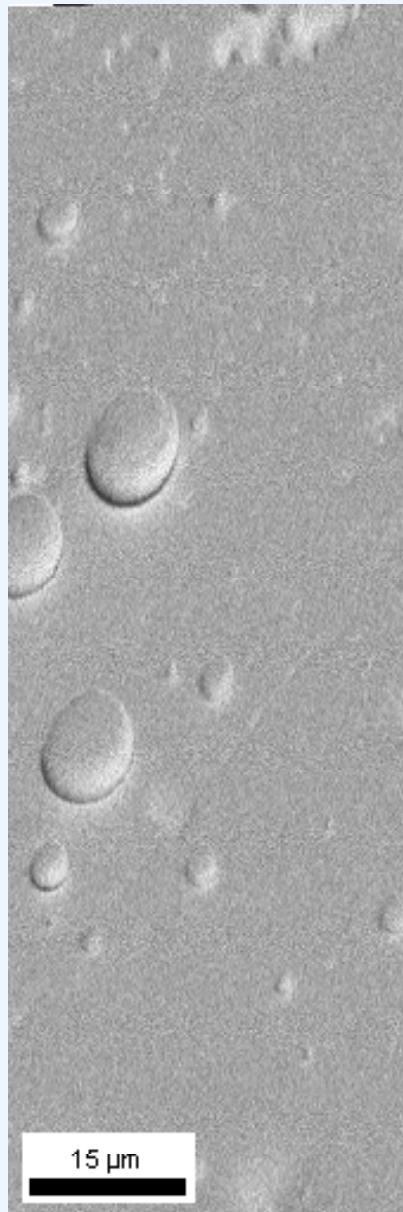




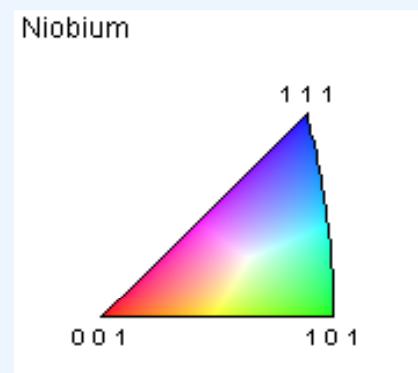
*The AASC/JLab/NSU team hopes to  
continue our methodical investigation of  
Nb and other thin film SRF candidates,  
culminating in high field cavity tests  
after better understanding*



*Macroparticles of Nb appear to capture  
surface properties!*



*EBSD IPF View of  
Sample DOE-138-08B  
Substrate: "UNS C 10100  
Quarter Hard"*



Average C.I. 0.44

*Energetic Nb Ion  
Species Might  
Promote Long-  
Range Surface  
Diffusion, Thus  
Reconciling  
Macroparticles'  
Surface Crystal  
Orientation to Cu  
Substrate?*